AMENDED CLAIM SET:

1. (currently amended) A polishing composition comprising an abrasive having an average primary particle size of 200 nm or less, an oxidizing agent, an acid having a pK1 of 2 or less and/or a salt of an acid having as pK1 of 2 or less, and water, wherein the acid having a pK1 of 2 or less and/or the salt of an acid having a pK1 of 2 or less is selected from the group consisting of ~~sulfurous acid,~~ persulfuric acid, ~~phosphoric acid, phosphonic acid, phosphinic acid,~~ pyrophosphoric acid, and tripolyphosphoric acid ~~and amide sulfuric acid~~, and wherein the acid value (Y) of the polishing composition is 20 mg KOH/g or less and 0.2 mg KOH/g or more.

2. (original) The polishing composition according to claim 1, wherein the polishing composition has an acid value (Y) in the range 0.2 mg KOH/g through 5 mg KOH/g.

3. (original) The polishing composition of claim 1 or 2, wherein the acid value (Y) of the polishing composition satisfies the formula (1):

$$Y(\text{mg KOH/g}) \leq 5.7 \times 10^{-17} \times X(/g) + 19.45 \qquad (1)$$

wherein X is a concentration of the abrasive in the polishing composition on a numerical basis.

4. (original) A process for reducing the amount of fine scratches imparted to a substrate during a polishing operation, comprising polishing a substrate to be polished with the polishing composition of any one of claims 1 to 2.

5. (original) A process for reducing the amount of fine scratches imparted to a substrate during a polishing operation, comprising polishing a substrate to be polished with the polishing composition of claim 3.

6. (original) A method for manufacturing a substrate, comprising the step of polishing a substrate to be polished during a manufacturing process with the polishing composition of any one of claims 1 to 2.

7. (original) A method for manufacturing a substrate, comprising the step of polishing a substrate to be polished during a manufacturing process with the polishing composition of claim 3.